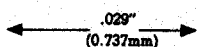
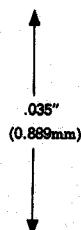
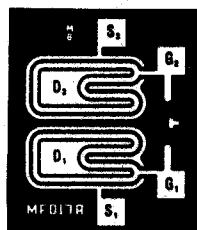


CHIP NUMBER

DFMPZ2



Die Size: 29 x 35 (mils)
 0.737 x 0.889(mm)
 5 x 5 (mils)
 Pad Size: 0.127 x 0.127(mm)
 BODY-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVDSS	-30		-60	V	VGS = 0, ID = -10µA
IDSS		-40	500	pA	VDS = -15V, VGS = 0, VBS = 0
gfs	1500		4000	µmho	VDS = -15V, ID = -10mA, f = 1KHz
ISDS			800	pA	VGS = 0, VSD = -15V, VDB = 0
rDS		220	350	Ω	VGS = -20V, ID = -100µA
VGS(th)	-1.5		-5.0	V	VDS = -15V, ID = -10µA, VBS = 0
Crss		1.0	1.5	pF	VDS = -15V, ID = -10mA, f = 1MHz
Ciss		3.5	4.5	pF	VDS = -15V, ID = -10mA, f = 1MHz
en		50		nV/√Hz	VDS = -15V, ID = -1mA, f = 1KHz
VGS(th) 1-2		25	100	mV	VDS = -15V, ID = -500µA

TYPICAL DEVICE TYPES: 3N188, 3N189

FIGURE 1

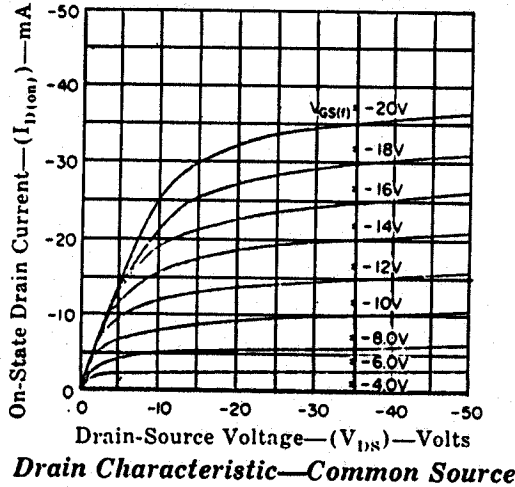


FIGURE 2

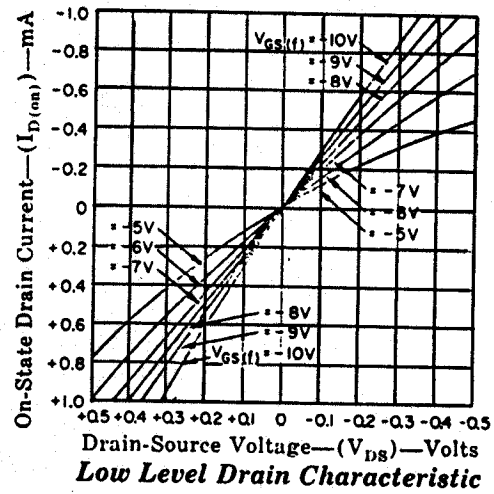


FIGURE 3

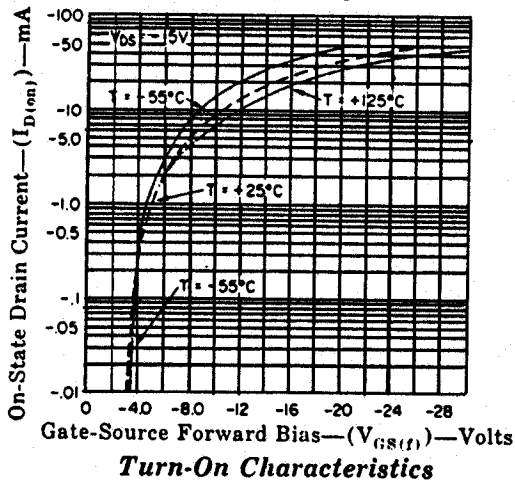


FIGURE 4

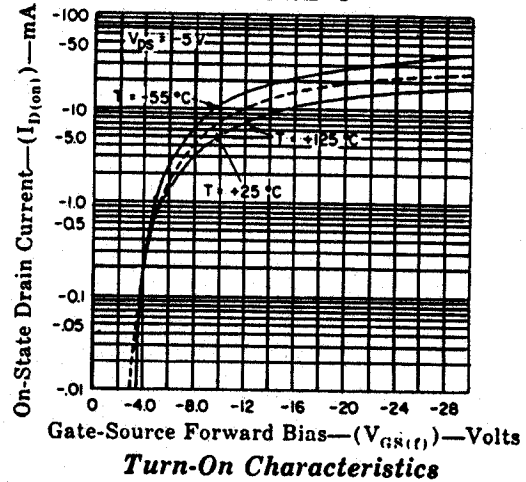


FIGURE 5

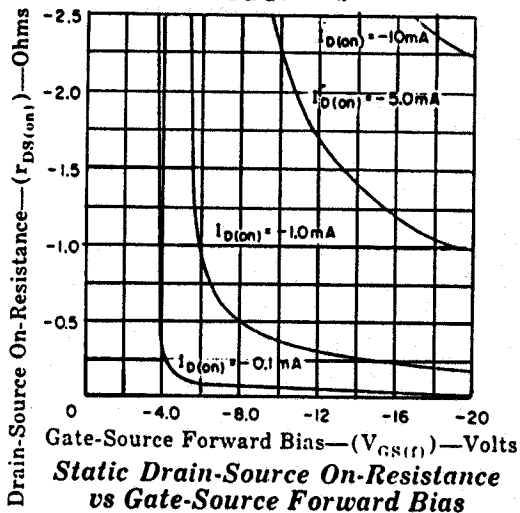


FIGURE 6

